

## VERSION WITH MARKINGS TO SHOW CHANGES MADE

### IN THE SPECIFICATION

Please replace the paragraph at page 5, line 30 to page 6, line 2, with the following:

Reference numerals 106', 110, and 114 denote a second dielectric layer, an inter-metal dielectric layer (IMD), and a passivation layer, respectively. These layers are dielectric layers used to sequentially form the second metal layer 112, the first metal layer 108, and the polysilicon film plate 104.

### IN THE CLAIMS

1. (Once amended) A bonding pad of a semiconductor device, said bonding pad comprising:

- a substructure formed on a semiconductor substrate;
- a first dielectric layer formed on the substructure;
- a polysilicon film plate formed on the first dielectric layer [and configured to improve the resistance of the bonding pad to stress induced during wire bonding];
- a second dielectric layer formed overlying the polysilicon film plate, the second dielectric layer having a first opening that expose a region of the polysilicon film plate,
- a first metal layer formed on the polysilicon film plate through the first opening;
- an inter-metal dielectric (IMD) layer formed overlying the first metal layer, the inter-metal dielectric layer having a second opening that exposes a region of the first metal layer;
- [and]
- a second metal layer formed on the first metal layer in the second opening; and
- a passivation layer formed overlying the second metal layer, the passivation layer having a third opening that exposes a region of the second metal layer as a bonding pad.

20. (Once amended) A bonding pad of a semiconductor device, said bonding pad comprising:

- a substructure formed on a semiconductor substrate;
- a first dielectric layer formed on the substructure;
- a polysilicon film plate formed on the first dielectric layer and configured to improve the resistance of the bonding pad to stress created during wire bonding;
- a first metal layer formed on the polysilicon film plate, wherein the first metal layer is formed having a recessed area; [and]

a second metal layer formed on the first metal layer, wherein a portion of the second metal layer is arranged within the recessed area of the first metal layer to improve the resistance of the bonding pad to stress; and

a passivation layer formed overlying the second metal layer having an opening that exposes the second metal layer as a bonding pad.

Claim 21 is new.